



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicants : Rhodes et. al  
Serial No. : 09/008,531  
Filed : January 16, 1998  
Title : METHOD OF MAKING A SEMICONDUCTOR DEVICE HAVING  
IMPROVED CONTACTS TO A THIN CONDUCTIVE LAYER  
Docket No. : MIO0012V2  
Examiner : EATON  
Art Unit : 2823

Box CPA  
Assistant Commissioner for Patents  
Washington, DC 20231

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TECHNOLOGY CENTER 2800

#11/B  
Amdt  
J. Mainelli  
5/24/00

Sir:

PRELIMINARY AMENDMENT

Please enter this amendment prior to any Office Actions. Reconsideration of the present application is respectfully requested in light of the remarks and amendments below.

IN THE CLAIMS

Please add new claims 31-39.

31. (New) A process for making a semiconductor device comprising:  
forming a layer of conductive material having a topography that includes a substantially vertical component;  
forming a contact disposed adjacent to and contacting said vertical component;  
and  
forming a structure having an opening therein under said conductive layer and filling said opening with said conductive material to form said vertical component.